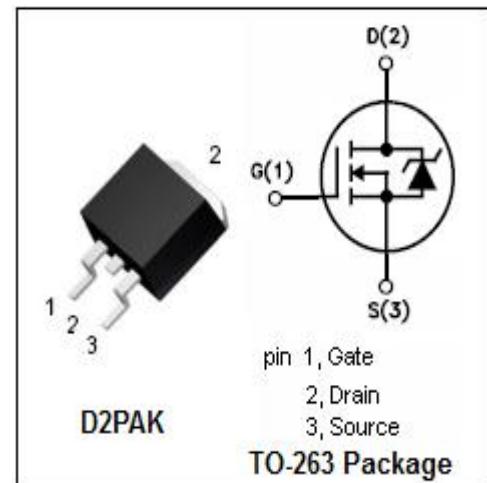


isc N-Channel MOSFET Transistor

R6024ENJ

• FEATURES

- With TO-263(D2PAK) packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



• APPLICATIONS

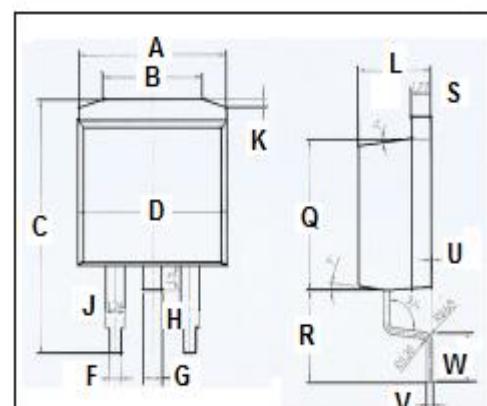
- Power supply
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GSS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous@ $T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$	24 13	A
I_{DM}	Drain Current-Single Pulsed	72	A
P_D	Total Dissipation	245	W
T_j	Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.51	$^\circ\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	80	$^\circ\text{C}/\text{W}$



DIM	mm	
	MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
O	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

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ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}; I_{\text{D}}= 1\text{mA}$	600			V
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}; I_{\text{D}}=1\text{mA}$	2.0		4.0	V
$R_{\text{DS}(\text{on})}$	Drain-Source On-Resistance	$V_{\text{GS}}= 10\text{V}; I_{\text{D}}=11.3\text{A}$		150	165	$\text{m}\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}; V_{\text{DS}}= 0\text{V}$			± 0.1	$\mu\text{ A}$
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}= 600\text{V}; V_{\text{GS}}= 0\text{V}; T_c=25^\circ\text{C}$ $T_c=125^\circ\text{C}$			100 1000	$\mu\text{ A}$
V_{SDF}	Diode forward voltage	$I_{\text{SD}}=24\text{A}, V_{\text{GS}} = 0 \text{ V}$			1.5	V

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